
R1LP0408C-I Series

Wide Temperature Range Version
4M SRAM (512-kword $\times$ 8-bit)

REJ03C0067-0200Z

Rev. 2.00

May.26.2004

Description

The R1LP0408C-I is a 4-Mbit static RAM organized 512-kword $\times$ 8-bit. R1LP0408C-I Series has realized higher density, higher performance and low power consumption by employing CMOS process technology (6-transistor memory cell). The R1LP0408C-I Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It has packaged in 32-pin SOP, 32-pin TSOP II.

Features

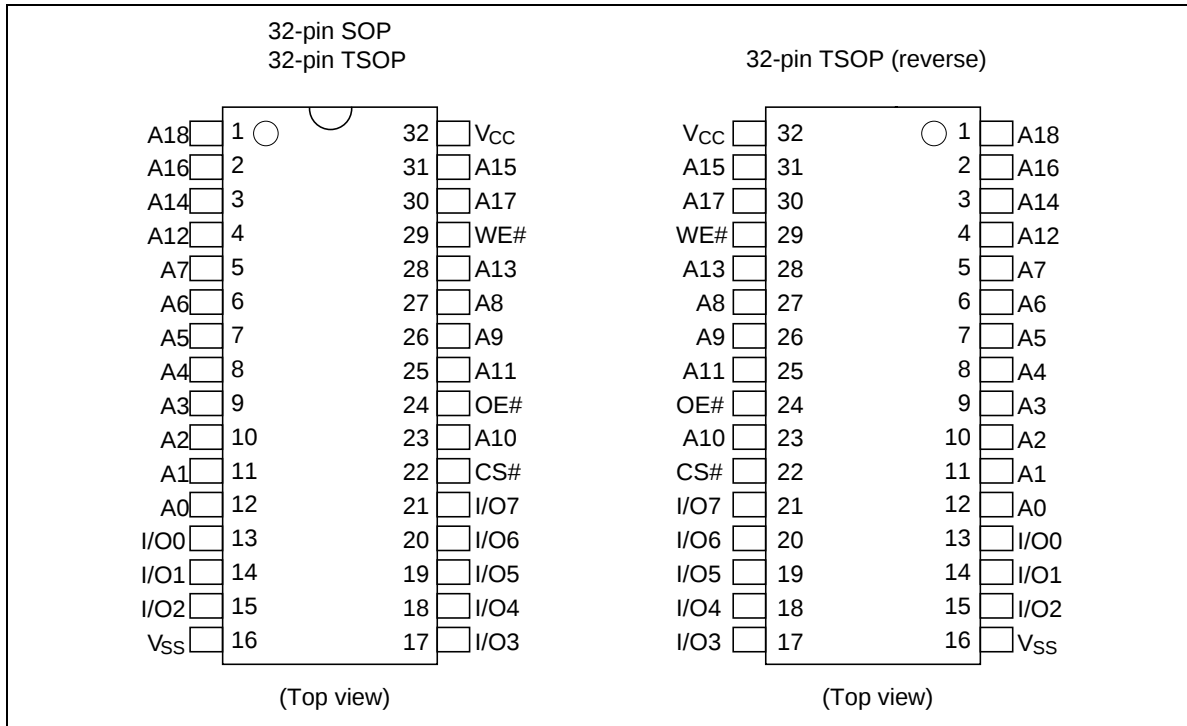
- Single 5 V supply: 5 V $\pm$ 10%
- Access time: 55/70 ns (max)
- Power dissipation:
 - Active: 10 mW/MHz (typ)
 - Standby: 4 μ W (typ)
- Completely static memory.
 - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
 - Three state output
- Directly TTL compatible.
 - All inputs and outputs
- Battery backup operation.
- Operating temperature: -40 to $+85^{\circ}\text{C}$

R1LP0408C-I Series

Ordering Information

Type No.	Access time	Package
R1LP0408CSP-5SI	55 ns	525-mil 32-pin plastic SOP (32P2M-A)
R1LP0408CSP-7LI	70 ns	
R1LP0408CSB-5SI	55 ns	400-mil 32-pin plastic TSOP II (32P3Y-H)
R1LP0408CSB-7LI	70 ns	
R1LP0408CSC-5SI	55 ns	400-mil 32-pin plastic TSOP II reverse (32P3Y-J)
R1LP0408CSC-7LI	70 ns	

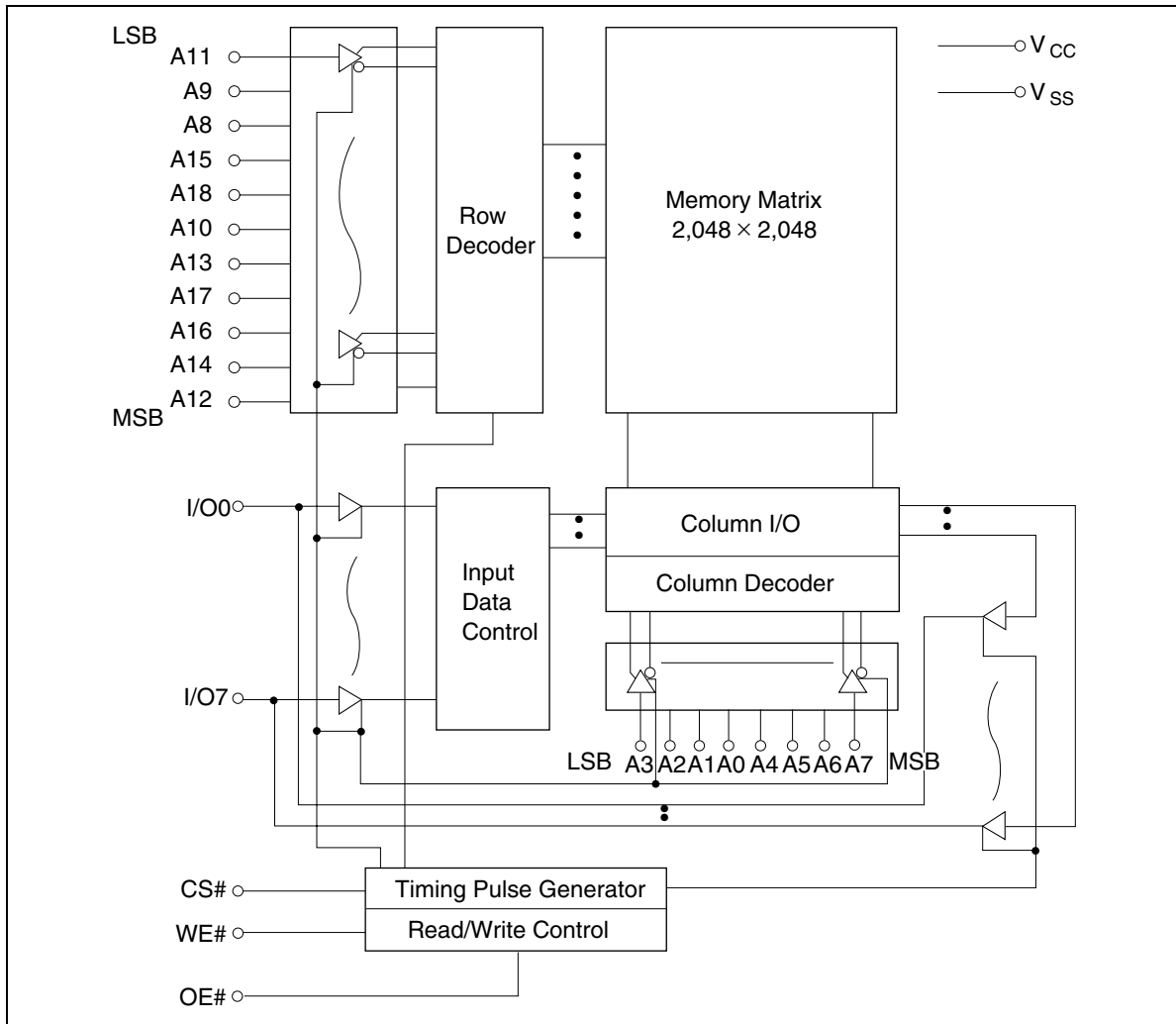
Pin Arrangement



Pin Description

Pin name	Function
A0 to A18	Address input
I/O0 to I/O7	Data input/output
CS# (CS)	Chip select
OE# (OE)	Output enable
WE# (WE)	Write enable
V _{CC}	Power supply
V _{SS}	Ground

Block Diagram



Operation Table

WE#	CS#	OE#	Mode	V _{CC} current	I/O0 to I/O7	Ref. cycle
×	H	×	Not selected	I _{SB} , I _{SB1}	High-Z	—
H	L	H	Output disable	I _{CC}	High-Z	—
H	L	L	Read	I _{CC}	Dout	Read cycle
L	L	H	Write	I _{CC}	Din	Write cycle (1)
L	L	L	Write	I _{CC}	Din	Write cycle (2)

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V _{SS}	V _{CC}	−0.5 to +7.0	V
Terminal voltage on any pin relative to V _{SS}	V _T	−0.5* ¹ to V _{CC} + 0.3* ²	V
Power dissipation	P _T	0.7	W
Operating temperature	T _{opr}	−40 to +85	°C
Storage temperature range	T _{stg}	−65 to +150	°C
Storage temperature range under bias	T _{bias}	−40 to +85	°C

Notes: 1. V_T min: −3.0 V for pulse half-width ≤ 30 ns.

2. Maximum voltage is +7.0 V.

DC Operating Conditions

(T_a = −40 to +85°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V _{CC}	4.5	5.0	5.5	V
	V _{SS}	0	0	0	V
Input high voltage	V _{IH}	2.2	—	V _{CC} + 0.3	V
Input low voltage	V _{IL}	−0.3* ¹	—	0.8	V

Note: 1. V_{IL} min: −3.0 V for pulse half-width ≤ 30 ns.

DC Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	
Input leakage current	$ I_{LI} $	—	—	1	μA	$V_{in} = V_{SS}$ to V_{CC}	
Output leakage current	$ I_{LO} $	—	—	1	μA	$CS\# = V_{IH}$ or $OE\# = V_{IH}$ or $WE\# = V_{IL}$ or $V_{I/O} = V_{SS}$ to V_{CC}	
Operating current	I_{CC}	—	1.5^{*1}	3	mA	$CS\# = V_{IL}$, Others = V_{IH}/V_{IL} , $I_{I/O} = 0$ mA	
Average operating current	I_{CC1}	—	8^{*1}	25	mA	Min. cycle, duty = 100%, $CS\# = V_{IL}$, Others = V_{IH}/V_{IL} , $I_{I/O} = 0$ mA	
	I_{CC2}	—	2^{*1}	5	mA	Cycle time = 1 μs , duty = 100%, $I_{I/O} = 0$ mA, $CS\# \leq 0.2$ V, $V_{IH} \geq V_{CC} - 0.2$ V, $V_{IL} \leq 0.2$ V	
Standby current	I_{SB}	—	0.1^{*1}	0.5	mA	$CS\# = V_{IH}$	
Standby current	-5SI	to +85°C	I_{SB1}	—	10	μA	$V_{in} \geq 0$ V, $CS\# \geq V_{CC} - 0.2$ V
		to +70°C	I_{SB1}	—	8	μA	
		to +40°C	I_{SB1}	—	1.0^{*2}	3	μA
		to +25°C	I_{SB1}	—	0.8^{*1}	3	μA
	-7LI	to +85°C	I_{SB1}	—	20	μA	
		to +70°C	I_{SB1}	—	16	μA	
		to +40°C	I_{SB1}	—	1.0^{*2}	10	μA
		to +25°C	I_{SB1}	—	0.8^{*1}	10	μA
Output low voltage	V_{OL}	—	—	0.4	V	$I_{OL} = 2.1$ mA	
Output high voltage	V_{OH}	2.4	—	—	V	$I_{OH} = -1.0$ mA	
	V_{OH2}	2.6	—	—	V	$I_{OH} = -0.1$ mA	

Notes: 1. Typical values are at $V_{CC} = 5.0 \text{ V}$, $T_a = +25^\circ\text{C}$ and specified loading, and not guaranteed.

2. Typical values are at $V_{CC} = 5.0 \text{ V}$, $T_a = +40^\circ\text{C}$ and specified loading, and not guaranteed.

Capacitance

($T_a = +25^\circ\text{C}$, $f = 1.0 \text{ MHz}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	Note
Input capacitance	C_{in}	—	—	8	pF	$V_{in} = 0 \text{ V}$	1
Input/output capacitance	$C_{I/O}$	—	—	10	pF	$V_{I/O} = 0 \text{ V}$	1

Note: 1. This parameter is sampled and not 100% tested.

R1LP0408C-I Series

AC Characteristics

(Ta = -40 to +85°C, V_{CC} = 5 V ± 10%, unless otherwise noted.)

Test Conditions

- Input pulse levels: V_{IL} = 0.4 V, V_{IH} = 2.4 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.5 V
- Output load: 1 TTL Gate + C_L (50 pF) (R1LP0408C-5SI)
1 TTL Gate + C_L (100 pF) (R1LP0408C-7LI)
(Including scope and jig)

Read Cycle

		R1LP0408C-I					
		-5SI		-7LI			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read cycle time	t _{RC}	55	—	70	—	ns	
Address access time	t _{AA}	—	55	—	70	ns	
Chip select access time	t _{CO}	—	55	—	70	ns	
Output enable to output valid	t _{OE}	—	25	—	35	ns	
Chip select to output in low-Z	t _{LZ}	10	—	10	—	ns	2
Output enable to output in low-Z	t _{OLZ}	5	—	5	—	ns	2
Chip deselect to output in high-Z	t _{HZ}	0	20	0	25	ns	1, 2
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1, 2
Output hold from address change	t _{OH}	10	—	10	—	ns	

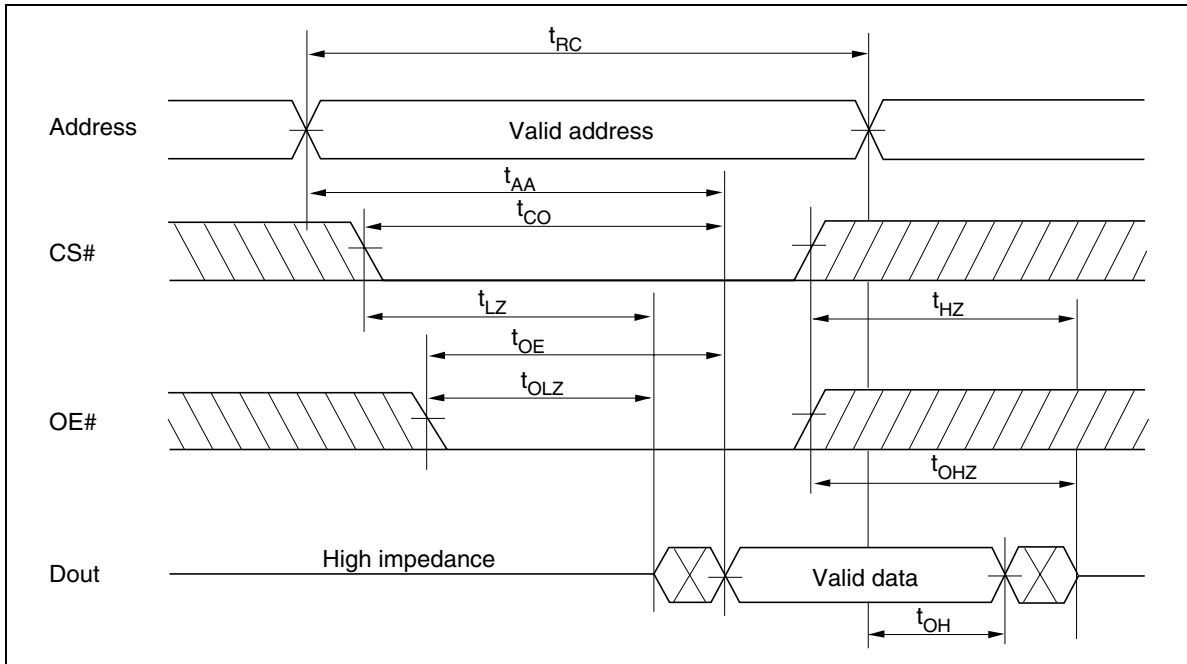
Write Cycle

		R1LP0408C-I					
		-5SI		-7LI			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write cycle time	t _{WC}	55	—	70	—	ns	
Chip selection to end of write	t _{CW}	50	—	60	—	ns	4
Address setup time	t _{AS}	0	—	0	—	ns	5
Address valid to end of write	t _{AW}	50	—	60	—	ns	
Write pulse width	t _{WP}	40	—	50	—	ns	3, 12
Write recovery time	t _{WR}	0	—	0	—	ns	6
Write to output in high-Z	t _{WHZ}	0	20	0	25	ns	1, 2, 7
Data to write time overlap	t _{DW}	25	—	30	—	ns	
Data hold from write time	t _{DH}	0	—	0	—	ns	
Output active from end of write	t _{OW}	5	—	5	—	ns	2
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1, 2, 7

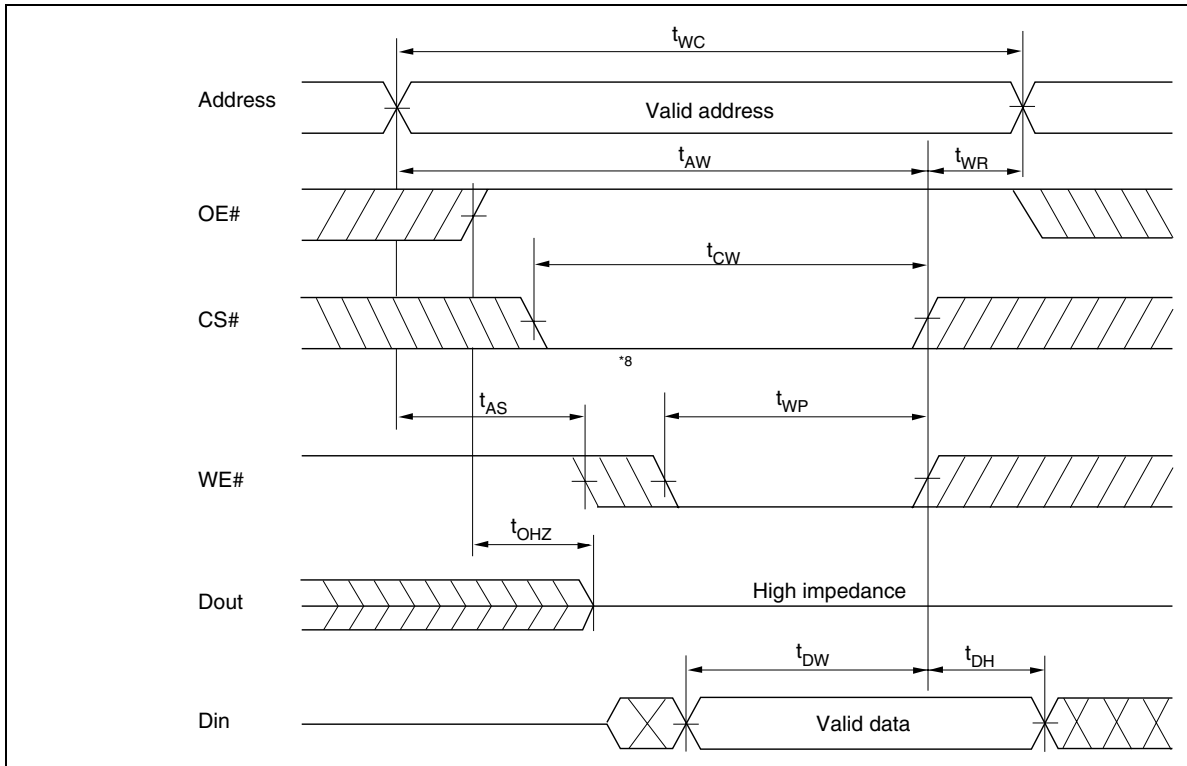
- Notes:
1. t_{HZ} , t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 2. This parameter is sampled and not 100% tested.
 3. A write occurs during the overlap (t_{WP}) of a low CS# and a low WE#. A write begins at the later transition of CS# going low or WE# going low. A write ends at the earlier transition of CS# going high or WE# going high. t_{WP} is measured from the beginning of write to the end of write.
 4. t_{CW} is measured from CS# going low to the end of write.
 5. t_{AS} is measured from the address valid to the beginning of write.
 6. t_{WR} is measured from the earlier of WE# or CS# going high to the end of write cycle.
 7. During this period, I/O pins are in the output state so that the input signals of the opposite phase to the outputs must not be applied.
 8. If the CS# low transition occurs simultaneously with the WE# low transition or after the WE# transition, the output remain in a high impedance state.
 9. Dout is the same phase of the write data of this write cycle.
 10. Dout is the read data of next address.
 11. If CS# is low during this period, I/O pins are in the output state. Therefore, the input signals of the opposite phase to the outputs must not be applied to them.
 12. In the write cycle with OE# low fixed, t_{WP} must satisfy the following equation to avoid a problem of data bus contention. $t_{WP} \geq t_{DW} \text{ min} + t_{WHZ} \text{ max}$

Timing Waveform

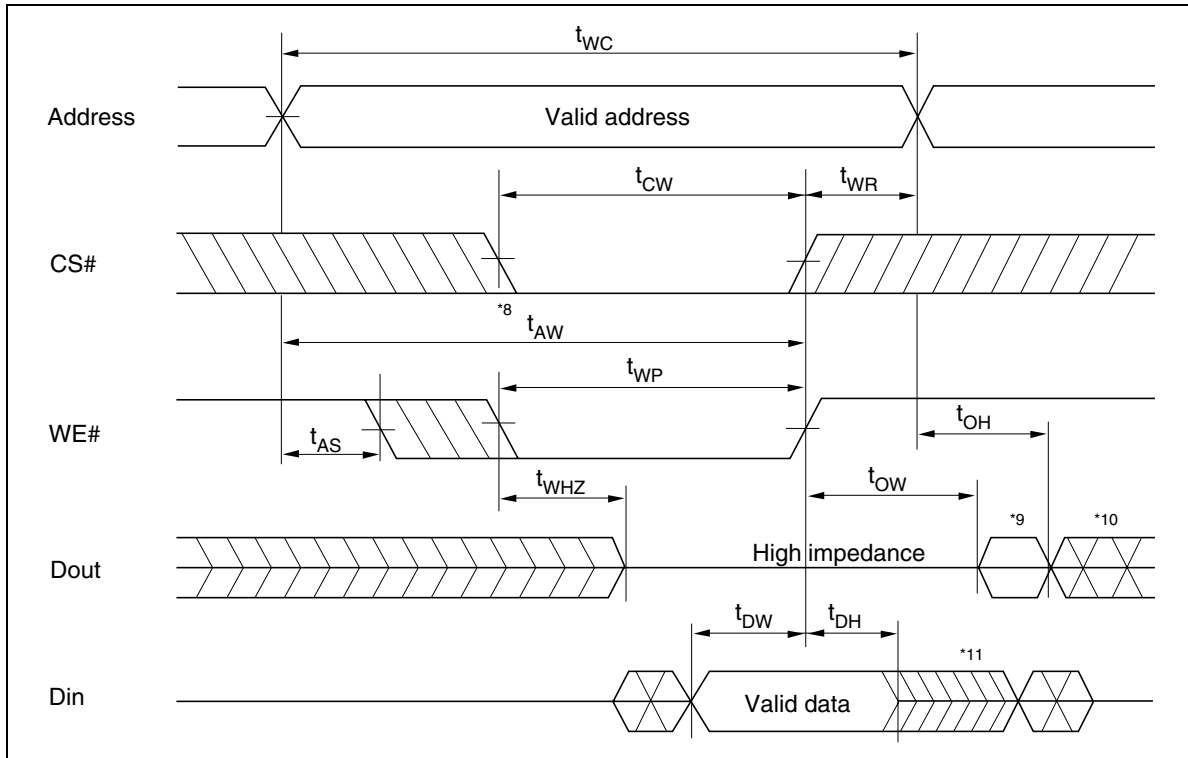
Read Timing Waveform ($WE\# = V_{IH}$)



Write Timing Waveform (1) (OE# Clock)



Write Timing Waveform (2) (OE# Low Fixed)



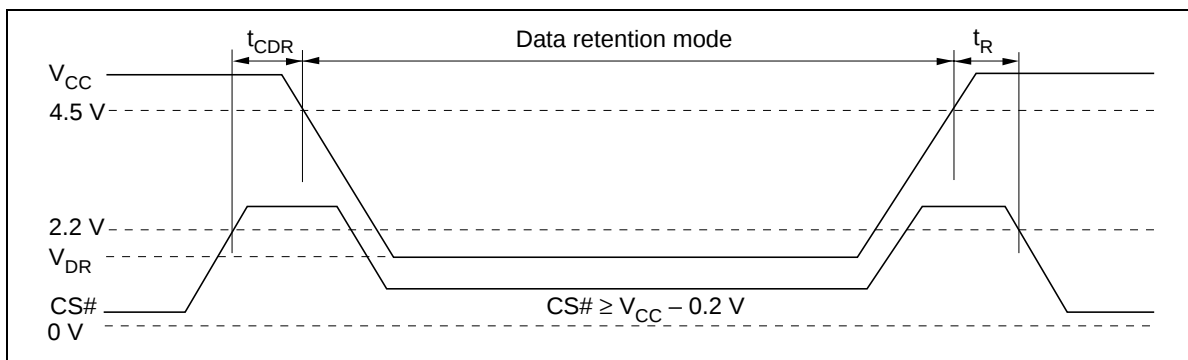
Low V_{CC} Data Retention Characteristics

($T_a = -40$ to $+85^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions* ³
V_{CC} for data retention	V_{DR}	2	—	—	V	$CS\# \geq V_{CC} - 0.2\text{ V}$, $V_{in} \geq 0\text{ V}$
Data retention current	-5SI	to $+85^\circ\text{C}$	I_{CCDR}	—	10	μA , $V_{CC} = 3.0\text{ V}$, $V_{in} \geq 0\text{ V}$
		to $+70^\circ\text{C}$	I_{CCDR}	—	8	μA , $CS\# \geq V_{CC} - 0.2\text{ V}$
		to $+40^\circ\text{C}$	I_{CCDR}	—	1.0^{*2}	3 μA
		to $+25^\circ\text{C}$	I_{CCDR}	—	0.8^{*1}	3 μA
	-7LI	to $+85^\circ\text{C}$	I_{CCDR}	—	20	μA
		to $+70^\circ\text{C}$	I_{CCDR}	—	16	μA
		to $+40^\circ\text{C}$	I_{CCDR}	—	1.0^{*2}	10 μA
		to $+25^\circ\text{C}$	I_{CCDR}	—	0.8^{*1}	10 μA
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t_R	t_{RC}^{*4}	—	—	ns	

- Notes: 1. Typical values are at $V_{CC} = 3.0\text{ V}$, $T_a = +25^\circ\text{C}$ and specified loading, and not guaranteed.
2. Typical values are at $V_{CC} = 3.0\text{ V}$, $T_a = +40^\circ\text{C}$ and specified loading, and not guaranteed.
3. $CS\#$ controls address buffer, $WE\#$ buffer, $OE\#$ buffer, and Din buffer. In data retention mode, V_{in} levels (address, $WE\#$, $OE\#$, I/O) can be in the high impedance state.
4. t_{RC} = read cycle time.

Low V_{CC} Data Retention Timing Waveform ($CS\#$ Controlled)



Revision History

R1LP0408C-I Series Data Sheet

Rev.	Date	Contents of Modification	
		Page	Description
1.00	Aug.01.2003	—	Initial issue
2.00	May.26.2004	6	DC characteristics –5SI and –7LI items' description are divided.
		12	Low V_{CC} Data Retention Characteristics –5SI and –7LI items' description are divided.
		12	Low V_{CC} Data Retention Timing Waveform 2.4 V to 2.2 V

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